

TE 364 LECTURE 5

Resonant Circuits

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Introduction



Resonant circuits are used in many applications such as

- *Filters
- *Oscillators
- **♦**Tuners
- tuned amplifiers
- *and microwave communication networks.



Resonant Circuits



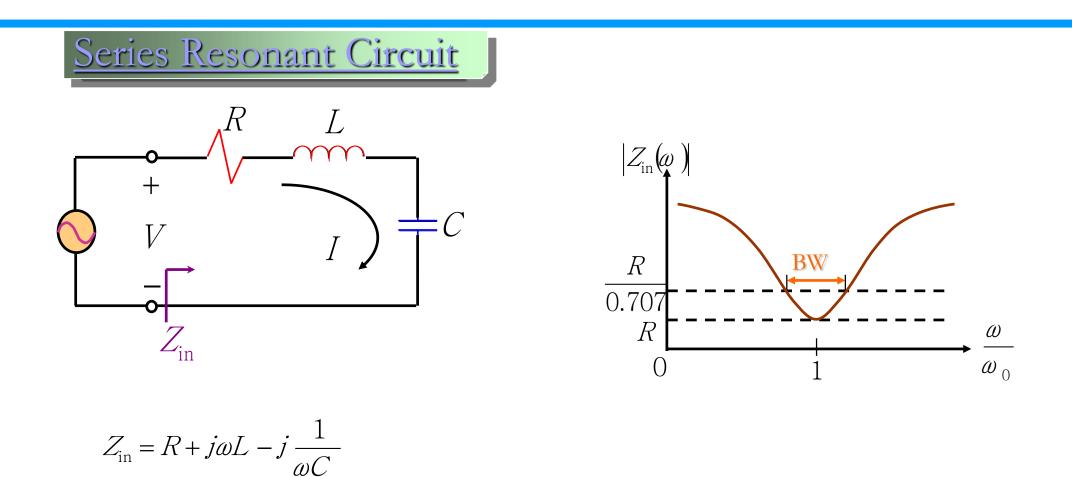
□Near resonance,

RF and microwave resonant circuits

- **C**an be represented either as
 - ✤a lumped element series or
 - parallel RLC networks.









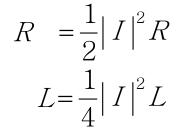


$$P_{in} = \frac{1}{2} VI^* = \frac{1}{2} Z_{in} I I^* = \frac{1}{2} Z_{in} |I|^2 = \frac{1}{2} V \left(\frac{V}{Z_{in}}\right)^* = \frac{1}{2} \frac{|V|^2}{Z_{in}^*}$$
$$= \frac{1}{2} |I|^2 \left(R + j\omega L - j\frac{1}{\omega C}\right)$$
(6.2)

 $P_{\rm loss}$ = Power dissipated by the resister

 W_m = Average magnetic energy stored in

$$W_{e} = \text{Average electric energy stored in}$$
$$= \frac{1}{4} |V_{C}|^{2} C = \frac{1}{4} \left| \frac{I}{j\omega C} \right|^{2} C = \frac{1}{4} |I|^{2} \frac{1}{\omega^{2} C}$$



C

 $\left(:: \mathcal{V}_{C} = \frac{1}{C} \int i dt \qquad V_{C} = \frac{I}{i\omega C}\right)$





$$P_{\rm in} = P_{\rm loss} + j \, 2\omega \left(W_m - W_e \right) \tag{6.5}$$

$$Z_{\rm in} = \frac{2P_{\rm in}}{|I|^2} = \frac{P_{\rm loss} + j 2\omega (W_m - W_e)}{|I|^2/2}$$

At resonance,
$$W_m = W_e$$

$$\therefore Z_{in} = \frac{P_{loss}}{|I|^2/2} = R \quad \text{(purely real)}$$

$$W_m = \frac{1}{4} |I|^2 L = W_e = \frac{1}{4} |I|^2 \frac{1}{\omega^2 C}$$

$$\Rightarrow \omega = \frac{1}{\sqrt{LC}} = \omega_0$$
 : resonant frequency

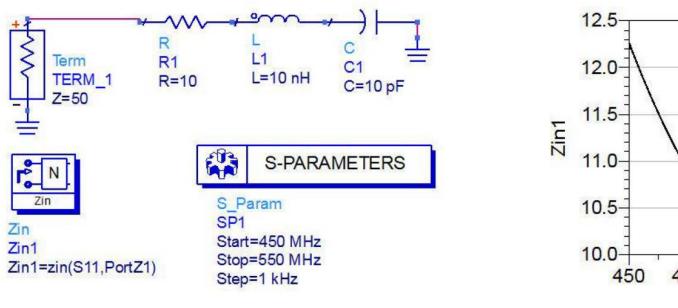
$$Z_{in} \longrightarrow Q_{in} \longrightarrow Q_{in}$$

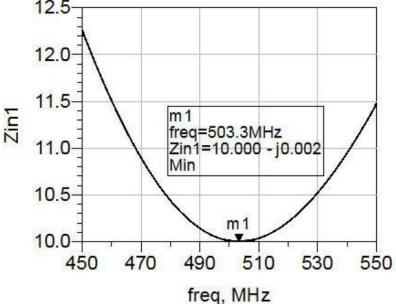
$$P_{in} = \frac{1}{2} |I|^{2} R$$

Nea resonance,
$$Z_{in} = j 2I\Delta \omega = j 2I(\omega - \omega_0)$$













Q (quality factor)

Quality Factor, Q of the series resonator is

$$Q = \omega \frac{(\text{ average energy stored })}{(\text{ energy loss/second })} = \omega \frac{W_m + W_e}{P_\ell}$$

At resonance, $W_m = W_e$

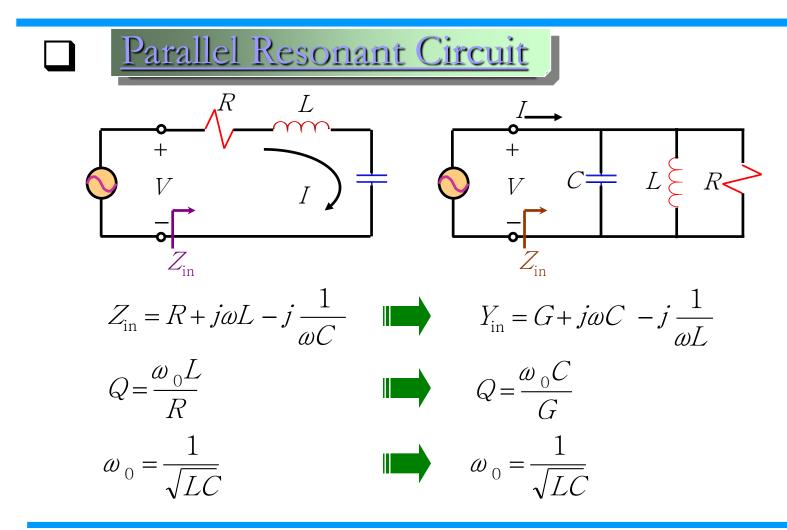
$$\therefore Q = \omega_0 \frac{2W_m}{P_\ell} = \omega_0 \frac{2\frac{1}{4} |I|^2 L}{\frac{1}{2} |I|^2 R} = \frac{\omega_0 L}{R} \left(= \frac{1}{\omega_0 RC} \right) \left(\because \omega_0 = \frac{1}{\sqrt{LC}} \right)$$

As R decreases, Q increases



Parallel Resonant Circuits

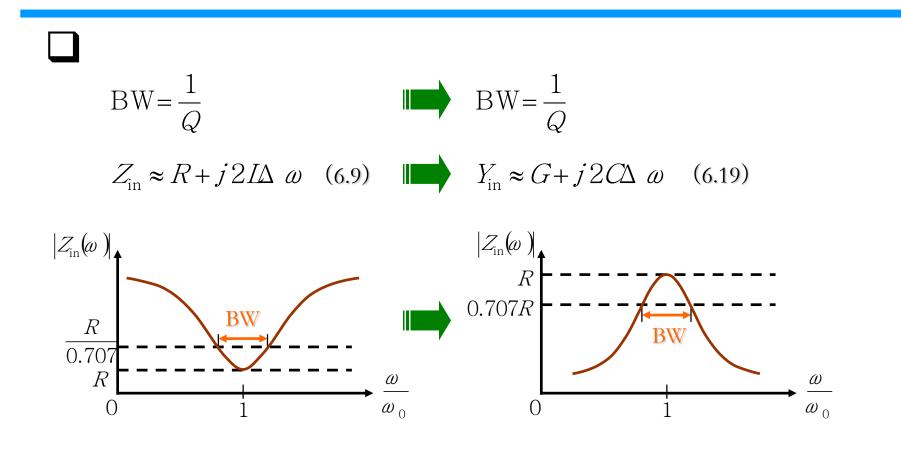






Parallel Resonant Circuits









If the AC voltage across the parallel resonant circuit is V,

then the complex power delivered to the resonator is

$$P_{in} = \frac{|V|^2}{2} Y_{in} = \frac{|V|^2}{2} \left(\frac{1}{R} + j\omega C - \frac{1}{j\omega L}\right)$$

At resonance

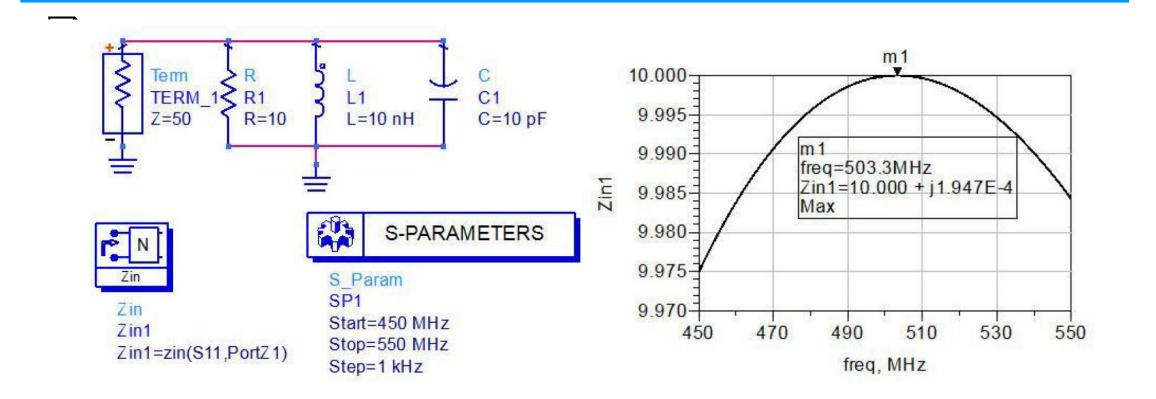
power dissipated in the resistor is

$$P_{in} = \frac{\left|V\right|^2}{2R} , \qquad \qquad \omega_o = \frac{1}{\sqrt{LC}}$$



Parallel Resonant Circuits









In the resonant circuits seen so far,

- \mathbf{A} the resistor R_1 represents the loss in the resonator.
- It includes the losses in
 - the capacitor as well as
 - the inductor.
- \Box The Q-factor is
 - the ratio of the energy stored in the inductor and capacitor to
 - the power dissipated in the resistor as a function of frequency





Generation For the series resonant circuit,

 \bullet the unloaded *Q*-factor is defined by:

$$Q_u = \frac{X}{R} = \frac{\omega_o L}{R} = \frac{1}{\omega_o CR}$$

 \Box The unloaded Q-factor of the parallel resonant circuit is simply

the inverse of the unloaded Q factor of the series resonant circuit.

$$Q_u = \frac{R}{X} = \frac{R}{\omega_o L} = \omega_o CR$$





UWe can clearly see that

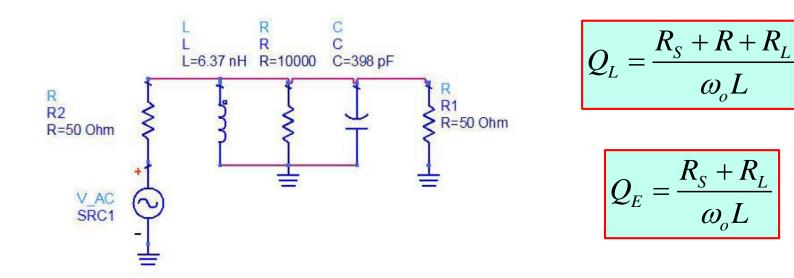
- *as the resistance increases in the series resonant circuit,
- the Q-factor decreases.
- Conversely,
 - \clubsuit as the resistance increases in the parallel resonant circuit,
 - the Q-factor increases.
- \Box The *Q*-factor is a measure of loss in the resonant circuit. Thus
 - *a higher Q corresponds to lower loss and
 - *a lower Q corresponds to a higher loss.





Loaded Q and External Q (Q_L and Q_e)

 \Box For the parallel resonator that is attached to a 50 Ω source and load as shown below







The three Q-factors are related by the inverse relationship of equation

$\frac{1}{Q_L} = \frac{1}{Q_u} + \frac{1}{Q_E}$

The loaded Q is also related to the fractional bandwidth as

$$Q_L = \frac{\sqrt{f_l f_h}}{BW_{-3dB}}$$

≻BW is the -3dB bandwidth,

 $\geq f_1$ and f_h are the lower and upper frequencies in Hz at -3dB points.





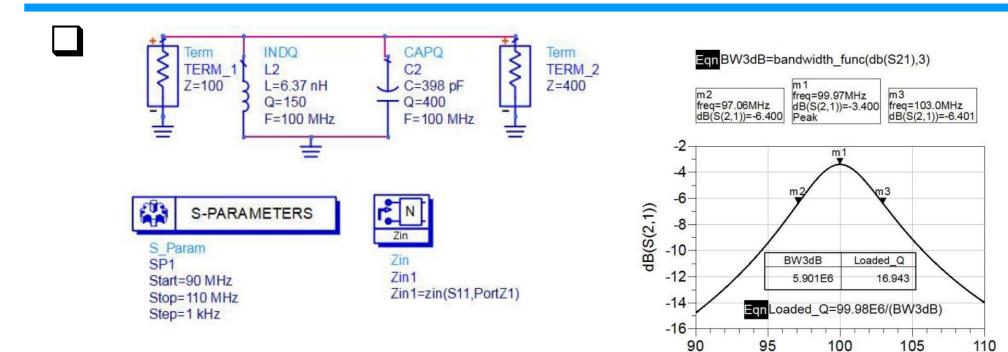


Design a lumped element parallel resonator at a frequency of 100 MHz. The resonator is intended to operate between a source resistance of 100 Ω and a load resistance of 400 Ω . use the ADS inductor and capacitor models that include the comp onent Q factor (L=6.37 nH, Q =150; C=398 pF, Q=400).





freq, MHz



The loaded Q can be calculated from

$$Q_L = \frac{\sqrt{f_l f_h}}{BW_{-3dB}} = \frac{99.98MHz}{5.901MHz} = 16.4$$





<u>Effect of Load Resistance on BW and QL</u>

- In RF circuits and systems
 - the impedances encountered are often quite low,
 - *ranging from 1 Ω to 50 Ω.
 - & It may not be practical to have a source impedance of 100 Ω and a load impedance of 400 Ω .
- \Box Lower resistances such as 50 Ω will
 - Lower the bandwidth and thus
 - Lower the loaded Q





<u>Effect of Load Resistance on BW and QL</u>

- To maintain the high Q of the resonator when attached to a load such as 50 Ω ,
 - tit is necessary to transform the low impedance to high impedance presented to the load.
 - The 50 Ω impedance can be transformed to the higher impedance of the parallel resonator thereby

➢ resulting in less loading of the resonator impedance.

This is referred to as loosely coupling the resonator to the load.





The tapped-capacitor and tapped-inductor networks

- can be used to accomplish this Q transformation in lumped element circuits.
- **C**Replacing the capacitor in the parallel network with a tapped capacitor, $C_T = \frac{C_1 C_2}{C_1 + C_2} \qquad R_{L1} = R_L \left(1 + \frac{C_1}{C_2}\right)^2$

 $> R_{L1}$ is the higher transformed load resistance (required for the high Q) $> R_L$ is the desired termination impedance, say 50 Ω $> C_T$ is simply the original capacitance and C1 and C2 results from tapping





A tapped inductor can also be used to the same effect at the source

$$R_{S1} = R_S \left(\frac{L_T}{L_1}\right)^2$$

$$L_T = L_1 + L_2$$



Practical Microwave Resonators



At higher RF and microwave frequencies

- small values of inductance and capacitance are physically unrealizable.
- So resonators are seldom realized with discrete lumped element RLC components.
- Even if the values could be physically realized the resulting Q factors would be unacceptably low for most applications.



Practical Microwave Resonators



At higher RF and microwave frequencies

- Resonators can be realized in all of the basic transmission line forms
- There are many specialized resonators such as
 - Ceramic dielectric resonator pucks that are coupled to a microstrip transmission line as well as
 - ≻Yittrium Iron Garnet spheres that are loop coupled to its load.
- These resonators are optimized for very high Q factors
- \clubsuit and may be tunable over a range of frequencies.





<u>Home Work</u>

- *In the parallel LC Example, change the load from 400 Ω to 50 Ω and re-examine the circuit's 3 dB bandwidth and Q_L .
- Rearrange the parallel LC network with the tapped capacitor network and Re-examine the circuit's 3 dB bandwidth and Q_L .
- *****Do same for the inductor and re-examine the circuit's 3 dB bandwidt h and Q_L .

